



## CLAIMS

1. A ceramic substrate, for a semiconductor producing/examining device, having a conductor formed inside thereof or on the surface thereof,  
5 wherein said ceramic substrate has been sintered such that a fractured section thereof exhibits intergranular fracture.
2. The ceramic substrate for a semiconductor producing/examining device according to claim 1,  
10 wherein an average diameter of ceramic grains of said fractured section is 0.5 to 10  $\mu\text{m}$ .
3. The ceramic substrate for a semiconductor producing/examining device according to claim 1,  
15 wherein an impurity element is locally distributed in boundaries of ceramic grains of said fractured section.
4. The ceramic substrate for a semiconductor producing/examining device according to claim 1,  
20 wherein thermal conductivity of said ceramic substrate is 100 W/m·K or more.
5. The ceramic substrate for a semiconductor producing/examining device according to claim 1,  
25 wherein said ceramic substrate is constituted such that:  
an impurity-existent area where an impurity element is locally distributed in triple points of crystal grains, and  
an impurity element-nonexistent area where an impurity  
30 is not locally distributed in the triple points of the crystal grains,

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Related Pending Application

Related Case Serial No: 101359,083

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